

Vishay Siliconix

COMPLIANT

HALOGEN

FREE

4 O Dual SPST Switches

DESCRIPTION

The DG2537, DG2538, and DG2539 are low voltage, precision dual SPST switches that can be operated in a single supply or in a dual supply configuration power supply with low power dissipation. The DG2537, DG2538 and DG2539 can switch both analog and digital signals within the power supply rail, and conduct well in both directions.

Fabricated with advance submicron CMOS process, these switches provide high precision low and flat ON resistance, low leakage current, low parasitic capacitance, and low charge injection.

The DG2537, DG2538 and DG2539 contain two independent Single Pole Single Throw (SPST) switches. Switch-1 and switch-2 are normally open for the DG2537 and normally closed for the DG2538. For the DG2539, switch-1 is normally open and switch-2 is normally closed with a Break-Before-Make switching timing.

The DG2537, DG2538 and DG2539 are the ideal switches for use in low voltage instruments and healthcare devices. fitting the circuits of low voltage ADC and DAC, analog front end gain control, and signal path control.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination.

As a further sign of Vishay Siliconix's commitment, the DG2537, DG2538 and D2539 are fully RoHS compliant and halogen-free.

FEATURES

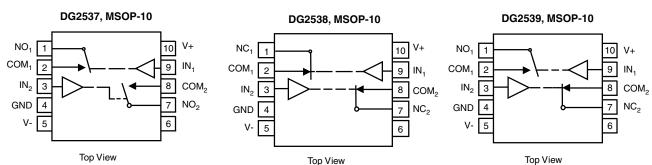
- Halogen-free According to IEC 61249-2-21 **Definition**
- Low and flat switch on resistance, 2.5 Ω /typ
- Low leakage and parasitic capacitance
- 366 MHz, 3 dB bandwidth
- Latch-up current > 300 mA (JESD78)
- Over voltage tolerant TTL/CMOS compatible
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Healthcare and medical devices
- Test instruments
- Portable meters
- Data acquisitions
- PDAs and modems
- Audio, video systems

- Control and automation
- Communication systems
- Mechanical reed relay replacement

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE (DG2537, DG2538)						
	DG2537	DG2538	Switches			
Logic	0	1	Off			
	1	0	On			

TRUTH TABLE (DG2539)						
Logic	Switch-1	Switch-2				
0	Off	On				
1	On	Off				

ORDERING INFORMATION							
Temperature Range	Package	Part Number					
	MSOP-10	DG2537DQ-T1-GE3					
- 40 °C to 85 °C	MSOP-10	DG2538DQ-T1-GE3					
	MSOP-10	DG2539DQ-T1-GE3					

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DG2537, DG2538, DG2539

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ABSOLUTE MAXIMUM RATINGS							
Parameter	Limit	Unit					
Referenced V+ to GND		- 0.3 to 6	V				
IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)						
Continuous Current (Any Terminal)	± 50	m A					
Peak Current (Pulsed at 1 ms, 10 % dut	± 200	mA					
Storage Temperature (D Suffix)	- 65 to 150	°C					
Power Dissipation (Packages) ^b	MSOP-10 ^c	320	mW				

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 4 mW/°C above 70 °C.

SPECIFICATIONS (V	T = 0 V, V	Test Conditions			Limits		
		Otherwise Unless Specified			°C to 85		
Parameter	Symbol	$V+ = 3 V$, $V- = 0 V$, $\pm 10 \%$, $V_{IN} = 0.4 V$ or 1.5 V^e	Temp.a	Min. ^b	Typ. ^c	Max.b	Unit
Analog Switch			_		T	T	
Analog Signal Range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0		V+	V
On-Resistance	R _{ON}	V+ = 2.7 V, V- = 0 V, $V_{COM} = 0 \text{ V to V+, I}_{NO}, I_{NC} = -10 \text{ mA}$	Room Full		6.5	10	
R _{ON} Flatness ^d	R _{ON} Flatness	V+ = 2.7 V, V- = 0 V, V _{COM} = 1.1 V to 1.6 V, I _{NO} , I _{NC} = - 10 mA	Room		0.4		Ω
R _{ON} Match ^d	R _{ON} Match	V+ = 2.7 V, V- = 0 V, $V_D = 1.1 \text{ V to } 1.6 \text{ V, } I_D = -10 \text{ mA}$	Room Full		0.3	0.9	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V, V- = 0 V,	Room Full	- 0.25 - 0.35		0.25 0.35	
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V/3 V}$, $V_{COM} = 3 \text{ V/1 V}$	Room Full	- 0.25 - 0.35		0.25 0.35	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 3.3 V, V- = 0 V, $V_{NO}, V_{NC} = V_{COM} = 1 \text{ V/3 V}$		- 0.25 - 0.35		0.25 0.35	
Digital Control							
Input High Voltage	V _{INH}		Full	2			V
Input Low Voltage	V _{INL}		Full			0.4	V
Input Capacitance ^d	C _{in}	f = 1 MHz	Full		2.4		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time	t _{ON}	V_{NO} or V_{NC} = 2 V, R_L = 300 Ω , C_L = 35 pF,	Room Full		16	55	ns
Turn-Off Time	t _{OFF}	figures 1 and 2	Room Full		7	40	113
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ figure } 3$	Room		1.8		рC
Bandwidth ^d	BW	$V+ = 3 V, R_L = 50 \Omega, C_L = 5 pF, -3dB$	Room		319		MHz
Off-Isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 67		
Crosstalk ^d	X _{TALK}	11 = 30 12, 0 = 3 ρ1, 1 = 1 Μ112	Room		- 92		٩D
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 10 MHz$	Room		- 47		dB
Crosstalk ^d	X _{TALK}	R _L = 50 Ω, C _L = 5 pr, 1 = 10 MHZ			- 90		1
Source-Off Capacitance ^d	C _{NC/NO(off)}		Room		8		
Drain-Off Capacitance ^d	C _{COM(off)}	$V_{IN} = 0$ or $V+$, $f = 1$ MHz	Room		9		pF
Channel-On Capacitance ^d	C _{ON}		Room		22		
Power Supply							
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+, V+ = 3.3 \text{ V}$				1	μΑ



		Test Conditions		Limits - 40 °C to 85 °C		°C	_
Parameter	Symbol	Otherwise Unless Specified $V+=5 \text{ V}, V-=0 \text{ V}, \pm 10 \text{ %}, V_{\text{IN}}=0.8 \text{ V or } 2.4 \text{ V}^{\text{e}}$	Temp. ^a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch		.,			7 -		
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
On-Resistance	R _{ON}	V+ = 4.5 V, V- = 0 V, $V_{COM} = 0 \text{ V to V+, I}_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		2.5	4.5 5	
R _{ON} Flatness ^d	R _{ON} Flatness	$V_{+} = 4.5 \text{ V}, V_{-} = 0 \text{ V},$ $V_{COM} = 1.3 \text{ V to 3 V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.75	1.5	Ω
R _{ON} Match ^d	R _{ON} Match	V+ = 4.5 V, V- = 0 V, $I_D = 10 \text{ mA}, V_{COM} = 1.3 \text{ V to 3 V}$	Room		0.2	0.9	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V, V- = 0 V,	Room Full	- 0.25 - 0.35		0.25 0.35	
	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V}/1 \text{ V}$	Room Full	- 0.25 - 0.35		0.25 0.35	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V- = 0 V, $V_{NO}, V_{NC} = V_{COM} = 1 \text{ V}/4.5 \text{ V}$	Room Full	- 0.25 - 0.35		0.25 0.35	
Digital Control							
Input High Voltage	V_{INH}		Full	2.4			V
Input Low Voltage	V_{INL}		Full			0.8	V
Input Capacitance	C _{in}	f = 1 MHz	Full		2.2		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0$ or V+	Full	- 0.1	0.005	0.1	μΑ
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω , C_L = 35 pF,	Room Full		17	30 40	ns
Turn-Off Time ^d	t _{OFF}	figures 1 and 2	Room Full		9	35	
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ figure 3}$	Room		2.2		рC
Bandwidth ^d	BW	$V+ = 5 V$, $R_L = 50 \Omega$, $C_L = 5 pF$, - 3 dB	Room		366		MHz
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 67		
Crosstalk ^d	X _{TALK}	nt = 50 24 Ot = 5 pr, 1 = 1 Minz	Room		- 90		1
Off-Isolation ^d	OIRR	D 5000 5 75 \$ 10 MHz	Room		- 47		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	Room		- 90		1
Source-Off Capacitance ^d	C _{NC/NO(off)}		Room		8		
Drain-Off Capacitance ^d	C _{COM(off)}	$V_{IN} = 0$ or $V+$, $f = 1$ MHz	Room		9		pF
Channel-On Capacitance ^d	C _{ON}	1			22		
Power Supply							1
Power Supply Range	V+			2.6		4.3	V
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+, V+ = 5.5 V$	Full			2	μΑ

DG2537, DG2538, DG2539

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		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °		°C	°C
Parameter	Symbol	$V+ = + 2.5 \text{ V}, V- = - 2.5 \text{ V}, \pm 10 \%,$ $V_{IN} = 0.8 \text{ V or } 2.4 \text{ V}^e$	Temp.a	Min.b	Typ. ^c	Max.b	Unit
Analog Switch		IIV	•		, ,,		
Analog Signal Range	V _{NO} , V _{NC} V _{COM}		Full	V-		V+	٧
On-Resistance	R _{ON}	$V+=+2.25 V, V-=-2.25 V, V_{COM}=V- to V+, I_{NO}, I_{NC}=10 mA$	Room Full		3.6	4.5 5	
R _{ON} Flatness	R _{ON} Flatness	$V+=+2.25 V, V-=-2.25 V, V_{COM}=\pm 1.2 V, 0 V, I_{NO}, I_{NC}=10 mA$	Room		0.7	1.5	Ω
R _{ON} Match	R _{ON} Match	V+ = + 2.25 V, V- = - 2.25 V, $V_{COM} = \pm 1.4 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.2	0.9	
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = + 2.75 V, V- = - 2.75 V,	Room Full	- 0.25 - 0.35		0.25 0.35	
Switch On Leakage Guirent	I _{COM(off)}	$V_S = \pm 2.5 \text{ V}, V_D = \pm 2.5 \text{ V}$	Room Full	- 0.25 - 0.35		0.25 0.35	nA
Switch on Leakage	I _{COM(on)}	$V+ = + 2.75 V$, $V- = - 2.25 V$, $V_S = V_D = \pm 2.5 V$	Room Full	- 0.25 - 0.35		0.25 0.35	
Digital Control							
Input High Voltage	V _{INH}		Full	2.4			\/
Input Low Voltage	V _{INL}		Full			0.8	V
Input Capacitance	C _{in}	f = 1 MHz	Full		2.2		pF
Input Current	I _{INL} or I _{INH}	$V_{IN} = 0$ or $V+$	Full	- 0.1		0.1	μΑ
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{NO} or $V_{NC} = 2 \text{ V}$, $R_{L} = 300 \Omega$, $C_{L} = 35 \text{ pF}$	Room Full			35 40	ns
Turn-Off Time ^d	t _{OFF}	*NO 5: *NC = 2 *, **:[= 555 22, 5[= 55 p:	Room Full			20 25	113
Charge Injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		2.2		рC
Bandwidth ^d	BW	$V+ = + 2.5 V$, $V- = -2.5 V$, $R_L = 50 \Omega$, $C_L = 5 pF$, $-3dB$	Room		366		MHz
Off-Isolation ^d	OIRR	V+ = + 2.5 V, V- = - 2.5 V,	Room		- 67		
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, - 3dB, $f = 1 MHz$	Room		- 90		1
Off-Isolation ^d	OIRR	V+ = + 2.5 V, V- = - 2.5 V,	Room		- 47		dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, - 3dB, $f = 10 MHz$	Room		- 90		1
Source-Off Capacitance ^d	C _{NC/NO(off)}		Room		6		
Drain-Off Capacitance ^d	C _{COM(off)}	$V_{IN} = 0$ or V+, $f = 1$ MHz	Room		12		pF
Channel-On Capacitanced	C _{ON}		Room		24		1
Power Supply	1		<u> </u>		1		
Power Supply Range	V+			1.25		2.75	V
Power Supply	I+	$V_{IN} = 0$ or V+, V+ = 2.5 V				2	μΑ

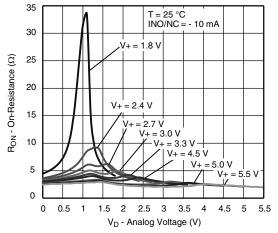
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Not production tested.

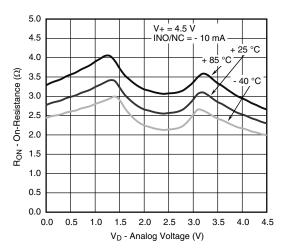
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



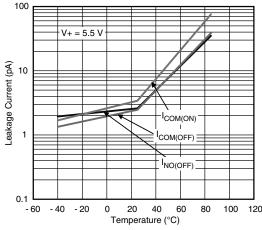
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



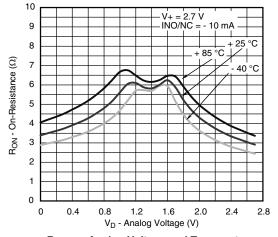
R_{ON} vs. V_D and Single Supply Voltage



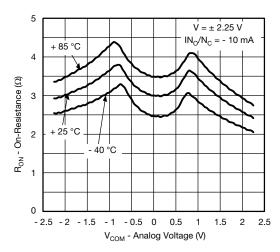
R_{ON} vs. Analog Voltage and Temperature



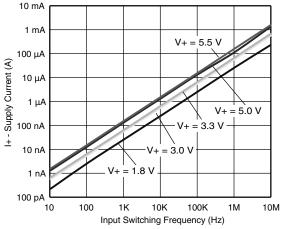
Leakage Current vs. Temperature



R_{ON} vs. Analog Voltage and Temperature



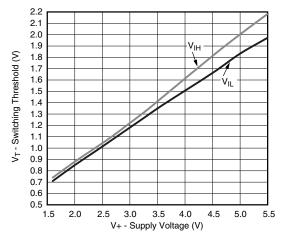
R_{ON} vs. Analog Voltage and Temperature



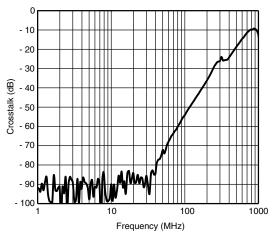
Supply Current vs. Input Switching Frequency

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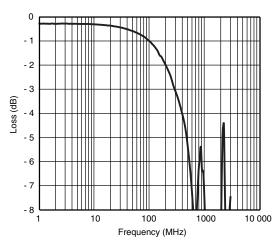
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



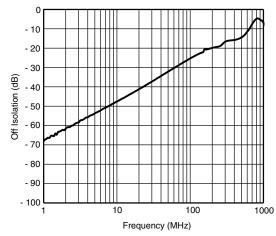
Switching Threshold vs. Supplz Voltage



Crosstalk vs. Frequency

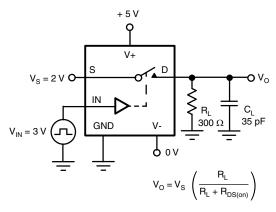


Insertion Loss vs. Frequency



Off Isolation vs. Frequency

TEST CIRCUITS



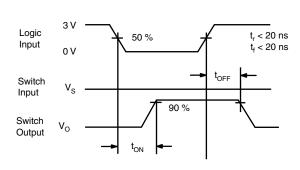


Figure 1. Single Supply Switching Time



TEST CIRCUITS

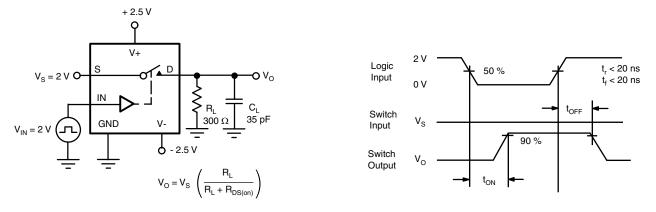
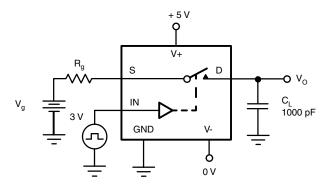
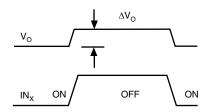


Figure 2. Dual Supply Switching Time





 ΔV_{O} = measured voltage error due to charge injection The charge injection in coulombs is ΔQ = C_{L} x ΔV_{O}

Figure 3. Charge Injection

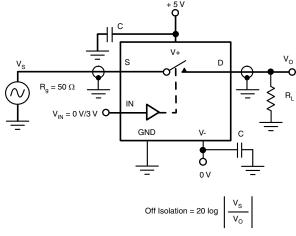


Figure 4. Off-Isolation

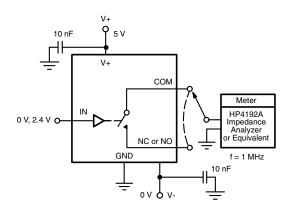


Figure 5. Channel Off/On Capacitance

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TEST CIRCUITS



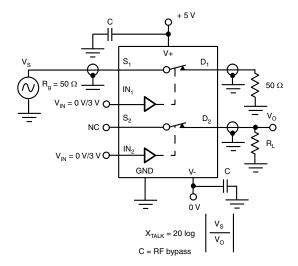


Figure 6. Channel to Channel Crosstalk

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63370.

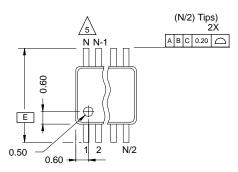




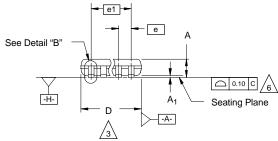


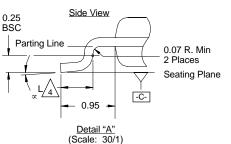
MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



Top View





NOTES:

. Die thickness allowable is 0.203 ± 0.0127.

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

3.

Dimensions "D" and "E $_1$ " do not include mold flash or protrusions, and are measured at Datum plane $\boxed{-H_2}$, mold flash or protrusions shall not exceed 0.15 mm per side.



Dimension is the length of terminal for soldering to a substrate.



Terminal positions are shown for reference only.



Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.



The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".



Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

9. Controlling dimension: millimeters.

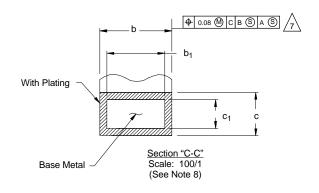
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

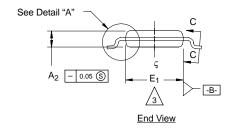


Datums —A— and —B— to be determined Datum plane —H—.

2 Exposed pad area in bottom side is the same as teh leadframe pad size.







N = 10L

	MI			
Dim	Min	Nom	Max	Note
Α	-	-	1.10	
A ₁	0.05	0.10	0.15	
A ₂	0.75	0.85	0.95	
b	0.17	-	0.27	8
b ₁	0.17	0.20	0.23	8
С	0.13	-	0.23	
c ₁	0.13	0.15	0.18	
D		3.00 BSC		3
Е		4.90 BSC		
E ₁	2.90	3.00	3.10	3
е		0.50 BSC		
e ₁		2.00 BSC		
L	0.40	0.55	0.70	4
N		10		5
œ	0°	4°	6°	
ECN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02		

Document Number: 71245

12-Jul-02



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Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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